

NPN SILICON RF TRANSISTOR

DESCRIPTION:

The **ASI MRF571** is Designed for low-noise, wide dynamic range front end amplifiers.

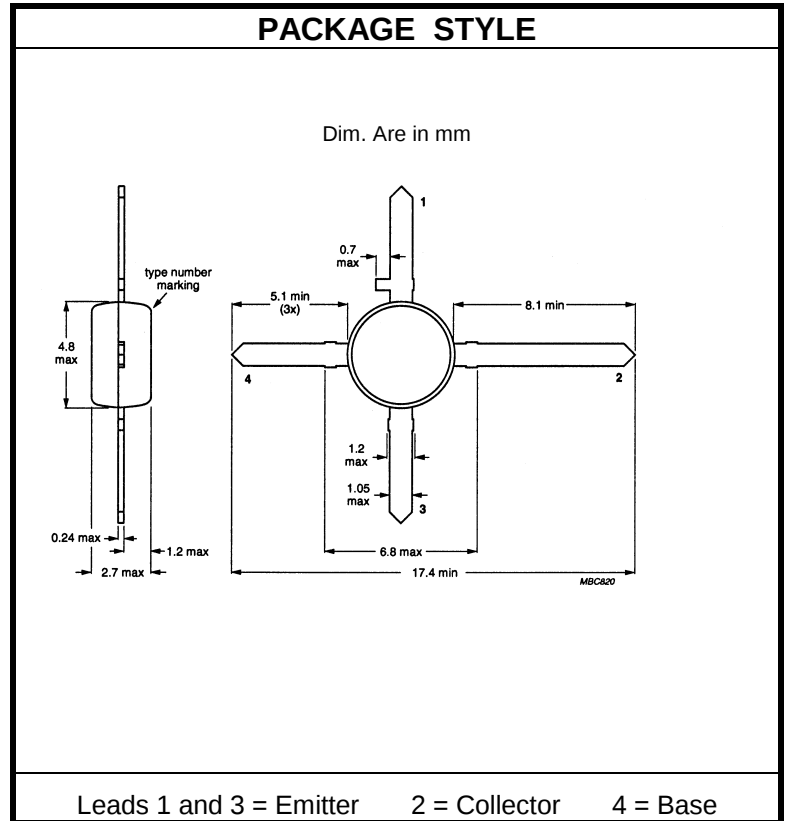
Applications up to 2.0 GHz.

FEATURES:

- Low Noise Figure
- High Gain
- **Omnigold™** Metalization System

MAXIMUM RATINGS

I_C	70 mA
V_{CBO}	20 V
V_{CEO}	10 V
V_{EBO}	3.0 V
P_{DISS}	1.0 W @ $T_C = 25\text{ }^{\circ}\text{C}$
T_J	-65 $^{\circ}\text{C}$ to +200 $^{\circ}\text{C}$
T_{STG}	-65 $^{\circ}\text{C}$ to +150 $^{\circ}\text{C}$



CHARACTERISTICS $T_C = 25\text{ }^{\circ}\text{C}$

SYMBOL	TEST CONDITIONS			MINIMUM	TYPICAL	MAXIMUM	UNITS
BV_{CBO}	$I_C = 0.1\text{ mA}$			20			V
BV_{CEO}	$I_C = 1.0\text{ mA}$			10			V
BV_{EBO}	$I_E = 500\text{ }\mu\text{A}$			2.5			V
I_{CBO}	$V_{CB} = 8.0\text{ V}$					10	μA
h_{FE}	$V_{CE} = 5.0\text{ V}$	$I_C = 30\text{ mA}$		50		300	---
C_{cb}	$V_{CB} = 6.0\text{ V}$	$f = 1.0\text{ MHz}$			0.7	1.0	pF
G_{NF}	$V_{CE} = 6.0\text{ V}$	$I_C = 10\text{ mA}$	$f = 0.5\text{ GHz}$		16.5		dB
			$f = 1.0\text{ GHz}$	10	12		
			$f = 2.0\text{ GHz}$				
NF	$V_{CE} = 6.0\text{ V}$	$I_C = 10\text{ mA}$	$f = 0.5\text{ GHz}$		1.0	2.0	dB
			$f = 1.0\text{ GHz}$		1.5		
			$f = 2.0\text{ GHz}$		2.8		